L Number	Hits	Search Text	DB	Time stamp
- Namber		257/506	USPAT;	2002/10/31 14:32
			US-PGPUB;	
			EPO; JPO;	
		·	DERWENT;	
'			IBM_TDB	
-	164	438/\$.ccls. and trench and angle and	USPAT;	2003/04/09 18:20
		(radio adj frequency)	US-PGPUB;	
	,		EPO; JPO; DERWENT;	
1			IBM TDB	
l _	10	438/\$.ccls. and trench and angle and	USPAT;	2003/08/18 09:04
		(radio adj frequency) and polymer and	US-PGPUB;	
		(fluorocarbon adj gas)	EPO; JPO;	1
			DERWENT;	
			IBM_TDB	
-	81	438/\$.ccls. and CF and CHF	USPAT;	2002/11/01 08:03
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	43	257/347 and ((gate adj electrode) WITH	USPAT;	2002/11/01 08:57
		trench) and SOI	US-PGPUB;	
			EPO; JPO;	••
			DERWENT;	
		057/047	IBM_TDB	0000/11/01 00 55
-	88	257/347 and ((gate adj electrode) same	USPAT;	2002/11/01 08:58
		trench) and SOI	US-PGPUB; EPO; JPO;	
		·	DERWENT;	
			IBM TDB	
] _	215	((tetrafluoromethane or "CF.sub.4") near2	USPAT;	2003/04/08 08:41
		(trifluoromethane or "CHF.sub.3")) same	US-PGPUB;	
İ		ratio same (plasma or etch or etch\$3 or	EPO; JPO;	
		RIE) and 438/\$.ccls.	DERWENT;	
	21.6	//hat a 63 account have an HGD sub All \ account	IBM_TDB USPAT;	2003/04/08 08:25
-	316	((tetrafluoromethane or "CF.sub.4") near2 (trifluoromethane or "CHF.sub.3")) same	US-PGPUB;	2003/04/08 08:25
		ratio same (plasma or etch or etch\$3 or	EPO; JPO;	
		RIE)	DERWENT;	,
		,	IBM TDB	
_	178	((tetrafluoromethane or "CF.sub.4") near2	USPAT;	2003/04/07 17:53
i		(trifluoromethane or "CHF.sub.3")) same	US-PGPUB;	
		(trench) and 438/\$.ccls.	EPO; JPO;	
			DERWENT;	
_	716	438/\$.ccls. and (trench or (isolation adj	IBM_TDB USPAT;	2003/04/08 09:32
	/10	trench)) and angle and (dielectric adj	US-PGPUB;	2003,04,00 03.32
		material)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	25	438/207 and trench and angle	USPAT;	2003/04/08 10:08
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	18	438/219 and trench and angle	USPAT;	2003/04/08 10:12
		in the second se	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		1,00,000	IBM_TDB	0000 (01 (00 15 15
-	70	438/221 and trench and angle	USPAT;	2003/04/08 10:36
1			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	32	438/218 and trench and angle	USPĀT;	2003/04/08 10:47
		_	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	<u> </u>

_	17	438/225 and trench and angle	USPAT; US-PGPUB;	2003/04/08 10:54
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	42	438/294 and trench and angle	USPAT;	2003/04/08 10:59
		Too, 251 and 0201011 and unight	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	158	438/296 and trench and angle	USPAT;	2003/04/08 13:21
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1	420/007	IBM_TDB	0000 (04 (00 10 00
-	40	438/297 and trench and angle	USPAT;	2003/04/08 13:29
		·	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	41	438/404 and trench and angle	USPAT;	2003/04/08 13:48
	7+	1 430/404 and crench and angle	US-PGPUB;	2003/04/00 13.40
1			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	262	438/424 and trench and angle	USPAT;	2003/04/08 14:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	57	438/425 and trench and angle	USPAT;	2003/04/08 14:25
		*	US-PGPUB;	
			EPO; JPO;	
		· ·	DERWENT;	
	110	420/427	IBM_TDB	0000 /04 /00 14 05
-	119	438/427 and trench and angle	USPAT;	2003/04/08 14:35
			US-PGPUB; EPO; JPO;	
			DERWENT;	
		·	IBM TDB	
-	25	438/439 and trench and angle	USPAT;	2003/04/08 14:38
			US-PGPUB;	2000, 01, 00 21,00
		·	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	104	257/506 and trench and angle	USPAT;	2004/09/14 10:43
			US-PGPUB;	
		*	EPO; JPO;	
			DERWENT;	
_	36	257/500 and tropph and angle	IBM_TDB	2002/04/00 14 42
-	36	257/508 and trench and angle	USPAT; US-PGPUB;	2003/04/08 14:48
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	139	257/510 and trench and angle	USPAT;	2003/07/28 08:30
		and cronon and angre	US-PGPUB;	2000,01,20 00.50
		,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	134	((side adj wall) with polymer) and trench	USPĀT;	2003/08/15 15:55
1		·	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	1592	(side adj wall) with polymer	USPAT;	2003/08/15 15:51
	1		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

188 ((side adj wall) with polymer) and trench and tetching and etching C((side adj wall) with polymer) with trench with etching C((side adj wall) with polymer) with trench with etching C((side adj wall) with polymer) with trench with etching C((side adj wall) with polymer) with trench C((side adj wall) with polymer) C((side adj wall) C((side adj wall) with polymer) C((side adj wall) with polymer) C((side adj wall) C((side adj wall) C((side adj wall)					
- 12 ((side adj wall) with polymer) with trench with etching with etching 2003/08/16 16:07 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,708 108,707 108,709 108,709 1		118	((side adj wall) with polymer) and trench	USPAT;	2003/08/15 15:56
- 12 ((side adj wall) with polymer) with trench with etching			and etching	1	
180 TOB 180 SPAT; with etching 180 TOB 180 SPAT; with etching 180 SPAT; with etching with gas with (radio adj 180 SPAT; with requency) 180 SPAT; with requency 180 SPAT; with reducing and one 180 SPAT; with reducing reducing 180 SPAT; with reducing 180	!				
- 122 ((side adj wall) with polymer) with trench USPAT: USPATURE PRO JPC) With etching with etching and checked and argon with the sching and checked and argon with etching and checked and argon with etching and checked and argon are proportionally and checked and argon are proportionally and controlled and checked and argon are proportionally and another proportionally and are proport		·		1	
With etching	_	12	((side adi wall) with polymer) with trench		2003/08/16 16:07
FPO, JPO; DCRWENT; IBM TDB USFAT; US-FGUB; PO JPO; DCRWENT; IBM TDB USFAT;		12			2003,00,10 10.07
- 59 438/s.ccls. and (benefits with masking) - 483 etching with gas with (radio adj USPAT; US-RGPUB; EPO, UPO) DERWENT; IBM TDB USPAT; US-RGPUB; EPO, UPO; DERWENT; USPAT;			With Ctelling		
Second S					
- 483 etching with gas with (radio adj EPO; JPO; JEO; JPO; JEO; JEO; JEO; JEO; JEO; JEO; JEO; JE				· ·	
- 483 etching with gas with (radio adj DERWENT; IBM TDB USPAT; US-PCFUB; EPO, JPO; DERWENT; IBM TDB USPAT; US-	_	59	438/\$.ccls. and (benefits with masking)		2003/08/16 16:10
- 483 etching with gas with (radio adj IBM TDB USPAT; US-FOFUB; EPO; JPO; DERWENT; US-FOFUB; EPO; JPO; JPO; DERWENT; US-FOFUB; EPO; JPO; JPO; DERWENT; US-FOFUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J					
- 483 etching with gas with (radio adj frequency) - 74 etching with ((tetrafluoromethane or "CF.sub.4") or (trifluoromethane or "CHF.sub.4") or (trifluorometh					
- 483 etching with gas with (radio adj frequency) - 74 etching with ((tetrafluoromethane or "CF.sub.4") or (trifluoromethane or "CF.sub.4") or (trifluoromethane or "CHF.sub.4")) with (radio adj frequency) - 53 257/314 and profile and floating and ONO ERWENT; IEM TOB USPAT; US-PGPUB; EPO, JPO; DERWENT; IEM TOB USPAT; US-PGPUB;				,	
Frequency SPERUB; EPO; JPO; DERMENT; IBM TOB USFAT; US-PGPUB; EPO; JPO; DERMENT; US-PGPUB; USFAT; U					
- 74 etching with ((tetrafluoromethane or "CF.sub.4") or (trifluoromethane or "CHF.sub.4") or (trifluoromethane or "CHF.sub.4") or (trifluoromethane or "CHF.sub.4") with (radio adj frequency) - 53 257/314 and profile and floating and ONO - 53 257/314 and profile and floating and ONO - 252 (flash adj memory) and amorphous and ONO and (trench\$2 or STI\$2) - 66 257/\$.ccls. and trench and (dielectric with (etching near (over-etching)) - 7 209 257/\$.ccls. and (mask\$4 with (uspar) (over-etching)) - 209 257/\$.ccls. and (mask\$4 with (uspar) (over-etching)) - 23 257/\$.ccls. and trench and angle and (over adj etching) - 23 (semiconductor adj substrate) and de-chuck\$ and argon - 36 etching and de-chuck\$ and argon - 37 438/\$.ccls. and (etch with ((over-etching)) (over adj etching)) with plasma) - 38 438/\$.ccls. and (etch with ((over-etching)) (over adj etching)) with plasma) - 39 438/\$.ccls. and (etch with ((over-etching)) (over adj etching)) with plasma)	-	483			2003/08/18 09:06
- 74 etching with ((tetrafluoromethane or "CF.sub.4") or (trifluoromethane or "CF.sub.4") or (trifluor			frequency)		
-					
- detching with ((tetrafluoromethane or "CF.sub.4") or (trifluoromethane or "CF.sub.4") or (trifluoromethane or "CF.sub.4") or (trifluoromethane or "CF.sub.3") with (radio adj frequency)			·		
"CF.sub.4") or (trifluoromethane or "CHF.sub.3")) with (radio adj frequency) EPO; JPO; DERWENT; IBM TDB USPAT; US-PCPUB; EPO; JPO; DERWENT; US-PCPUB; EPO; J	_	7.4	etching with //tetrafluoromothano or		2003/09/05 16:44
"CHF.sub.3")) with (radio adj frequency)	-	/4	"CF sub 4") or (trifluoromethane or		2003/03/03 16:44
- 53 257/314 and profile and floating and ONO USERT: IBM TDB USPAT: US-PGPUB: PO, JPO; DERWENT; IBM TDB USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; USPAT; USPAGPUB; EPO; JPO; DERWENT; USPA				1	
Samiconductor adj substrate and Cover Cover adj etching		1	land and troquency	1	
- 53 257/314 and profile and floating and ONO USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO					
US-PGPUB; EPO; JPO; DERWENT; IBM TDB 2003/09/05 17:34 US-PGPUB; EPO; JPO; DERWENT; IBM TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB;	-	53	257/314 and profile and floating and ONO		2003/09/05 17:31
- 252 (flash adj memory) and amorphous and ONO and (trench\$2 or STI\$2) - 66 (257/\$.ccls. and trench and (dielectric with (etching near (over-etching))) - 209 (257/\$.ccls. and (mask\$4 with (over-etching))) - 209 (257/\$.ccls. and (mask\$4 with (over-etching))) - 235 (257/\$.ccls. and (mask\$4 with (over-etching))) - 236 (257/\$.ccls. and (mask\$4 with (over-etching))) - 237 (semiconductor adj substrate) and de-chuck\$ - 15 (semiconductor adj substrate) and de-chuck\$ - 15 (semiconductor adj substrate) and de-chuck\$ - 16 (semiconductor adj substrate) and de-chuck\$ - 17 (semiconductor adj substrate) and de-chuck\$ - 18 (semiconductor adj substrate) and de-chuck\$ - 19 (semiconductor adj substrate) and de-chuck\$ - 2004/05/11 13:00 2004/05/11 13:00 2004/05/11 13:00 2004/05/11 13:10 2004/05/11 13:10 2004/05/11 13:10 2004/05/11 13:52 2004/05/11 13:52 2004/05/11 13:52 2004/05/11 13:52 2004/05/11 13:52 2004/05/11 13:52 2004/05/11 13:52 2004/05/11 13:52 2004/05/11 13:52 2004/05/11 13:52 2004/05/11 13:52				1	
TBM TOB		1			
- 252 (flash adj memory) and amorphous and ONO and (trench\$2 or STI\$2) - 66 257/\$.ccls. and trench and (dielectric with (etching near (over-etching))				DERWENT;	
and (trench\$2 or STI\$2) and (trench\$2 or STI\$2) US-PGPUB; EPO; JPO; DERWENT; IEM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWEN					
- 66 257/\$.ccls. and trench and (dielectric with (etching near (over-etching))) - 209 257/\$.ccls. and (mask\$4 with (over-etching)) - 235 257/\$.ccls. and trench and angle and (over adj etching) - 236 (semiconductor adj substrate) and de-chuck\$ - 15 (semiconductor adj substrate) and de-chuck\$ and argon - 36 etching and de-chuck\$ and argon - 37 438/\$.ccls. and (etch with ((over-etching)) - 38 438/\$.ccls. and (etch with ((over-etching)) - 39 66 67/\$.ccls. and trench and angle and (over adj etching)) with plasma) - 30 67/\$.ccls. and trench and angle and (over adj etching)) with plasma) - 30 6 67/\$.ccls. and trench and angle and (over adj etching)) with plasma) - 30 67/\$.ccls. and trench and angle and (over adj etching)) with plasma) - 30 6 67/\$.ccls. and trench and angle and (over adj etching)) with plasma) - 30 6 67/\$.ccls. and trench and angle and (over adj etching)) with plasma)	-	252		· ·	2003/09/05 17:34
- 66 257/\$.ccls. and trench and (dielectric with (etching near (over-etching)))			and (trench\$2 or STI\$2)		
- 66 257/\$.ccls. and trench and (dielectric with (etching near (over-etching))			· ·		
- 66 257/\$.ccls. and trench and (dielectric with (etching near (over-etching)) US-PGPUB; EPG, JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPG, JPO; DERWENT; EPG, JPO; DERWE					
with (etching near (over-etching))) - 209 257/\$.ccls. and (mask\$4 with (over-etching)) - 235 257/\$.ccls. and trench and angle and (over adj etching) - 236 (semiconductor adj substrate) and de-chuck\$ - 15 (semiconductor adj substrate) and de-chuck\$ and argon - 36 etching and de-chuck\$ and argon - 37 438/\$.ccls. and (etch with ((over-etching) or (over adj etching)) with plasma) - 38 VSPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US		66	257/6 cala and trough and (dialogtria		2004/05/11 09:06
EPC; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-P	-	00	l · · · · · · · · · · · · · · · · · · ·	· ·	2004/03/11 08:00
DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;			with (etching hear (over-etching)))	1	
TBM TDB USPAT; USPEQUB; EPO; JPO; DERWENT; IBM TDB USPAT; USPEQUB; EPO; JPO; DERWENT; IBM TDB USPAT; US					
Cover-etching US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DER				1	
EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DER	-	209	257/\$.ccls. and (mask\$4 with	USPAT;	2004/05/10 18:51
- 235 257/\$.ccls. and trench and angle and (over adj etching) - 23 (semiconductor adj substrate) and de-chuck\$ - 23 (semiconductor adj substrate) and de-chuck\$ - 15 (semiconductor adj substrate) and de-chuck\$ and argon - 36 etching and de-chuck\$ and argon - 37 438/\$.ccls. and (etch with ((over-etching) or (over adj etching)) with plasma) - 38 DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT;			(over-etching))		
- 235 257/\$.ccls. and trench and angle and (over adj etching) - 23 (semiconductor adj substrate) and de-chuck\$ - 15 (semiconductor adj substrate) and de-chuck\$ and argon - 36 etching and de-chuck\$ and argon - 37 438/\$.ccls. and (etch with ((over-etching) or (over adj etching)) with plasma) - 38 257/\$.ccls. and trench and angle and (over USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB;					
235 257/\$.ccls. and trench and angle and (over adj etching) USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; E				· ·	ļ
adj etching) S-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 23 (semiconductor adj substrate) and USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;	_	235			2004/05/11 14:15
- 23 (semiconductor adj substrate) and de-chuck\$ - 15 (semiconductor adj substrate) and de-chuck\$ - 15 (semiconductor adj substrate) and de-chuck\$ and argon - 36 etching and de-chuck\$ and argon - 37 438/\$.ccls. and (etch with ((over-etching) or (over adj etching)) with plasma) - 38 DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB			auj etcning)		
- 23 (semiconductor adj substrate) and de-chuck\$ - 15 (semiconductor adj substrate) and de-chuck\$ and argon - 15 (semiconductor adj substrate) and de-chuck\$ and argon - 36 etching and de-chuck\$ and argon - 37 438/\$.ccls. and (etch with ((over-etching) or (over adj etching)) with plasma) - 38 (semiconductor adj substrate) and USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
- 23 (semiconductor adj substrate) and de-chuck\$ 15 (semiconductor adj substrate) and de-chuck\$ and argon 15 (semiconductor adj substrate) and de-chuck\$ and argon 16 etching and de-chuck\$ and argon 17					
de-chuck\$ US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; ISPM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;	_	23	(semiconductor adi substrate) and		2004/05/11 13:00
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;		25	1 '		
- 15 (semiconductor adj substrate) and de-chuck\$ and argon - 36 etching and de-chuck\$ and argon - 37 438/\$.ccls. and (etch with ((over-etching) or (over adj etching)) with plasma) - 38 DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	1				
- 15 (semiconductor adj substrate) and de-chuck\$ and argon USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; Or (over adj etching)) with plasma) USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
de-chuck\$ and argon US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; Or (over adj etching)) with plasma) US-PGPUB; EPO; JPO; DERWENT;					, , , , , , , , , , , , , , , , , , ,
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	-	15			2004/05/11 13:10
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; Or (over adj etching)) with plasma) USPAT; US-PGPUB; EPO; JPO; DERWENT;			de-chuck\$ and argon		
- 36 etching and de-chuck\$ and argon - 39 438/\$.ccls. and (etch with ((over-etching) or (over adj etching)) with plasma) IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
- 36 etching and de-chuck\$ and argon USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; Or (over adj etching)) with plasma) USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	1				
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; Or (over adj etching)) with plasma) US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;		3.0	stabing and do shooks and arran		2004/05/11 12:52
EPO; JPO; DERWENT; IBM_TDB 438/\$.ccls. and (etch with ((over-etching) USPAT; US-PGPUB; EPO; JPO; DERWENT; or (over adj etching)) with plasma) EPO; JPO; DERWENT;	⁻	36	etening and de-chucks and argon	(2004/05/11 13:52
DERWENT; IBM_TDB USPAT; Or (over adj etching)) with plasma) US-PGPUB; EPO; JPO; DERWENT;					
- 39 438/\$.ccls. and (etch with ((over-etching) USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 39 438/\$.ccls. and (etch with ((over-etching) USPAT; 0r (over adj etching)) with plasma) US-PGPUB; EPO; JPO; DERWENT;					
or (over adj etching)) with plasma) US-PGPUB; EPO; JPO; DERWENT;	_	39	438/\$.ccls. and (etch with ((over-etching)		2004/05/11 15:37
EPO; JPO; DERWENT;					
DERWENT;			3.,,		
IBM TDB					

-	32		USPAT;	2004/05/11 15:20
		and ((nitride adj layer) and (oxide adj	US-PGPUB;	
		layer)))	EPO; JPO; DERWENT;	
			IBM TDB	
_	110	438/\$.ccls. and (etch and ((over-etching)	USPAT;	2004/09/10 14:56
		or (over adj etching)) with plasma)	US-PGPUB;	
			EPO; JPO;	`
			DERWENT;	
			IBM_TDB	0004400400
-	18	, , ,	USPAT;	2004/09/10 17:00
		plasma) and (magnetron))	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	12	257/\$.ccls. and ((masking adj layer) and	USPĀT;	2004/09/10 15:43
		(microwave same plasma) and (magnetron))	US-PGPUB;	-
			EPO; JPO;	
			DERWENT;	
	15	438/\$.ccls. and ((masking adj layer) and	IBM_TDB USPAT;	2004/09/10 15:48
-	13	(microwave same plasma) and (magnetron))	US-PGPUB;	2004/09/10 15:40
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	18		USPAT;	2004/09/11 14:26
1	`	(microwave same plasma) and (magnetron)	US-PGPUB;	
1			EPO; JPO;	
			DERWENT; IBM TDB	
	750	438/207	USPAT;	2004/09/14 10:50
	, 55	150, 20,	US-PGPUB;	2001, 03, 11 10100
	1		EPO; JPO;	
			DERWENT;	
		100/010	IBM_TDB	2224/22/24 22 54
_	393	438/218	USPAT;	2004/09/14 10:54
			US-PGPUB; EPO; JPO;	1
			DERWENT;	
			IBM TDB	
-	159	438/219	USPAT;	2004/09/14 10:57
			US-PGPUB;	
			EPO; JPO;	
		•	DERWENT;	
_	546	438/294	IBM_TDB USPAT;	2004/09/14 11:03
	340		US-PGPUB;	2004,03,14 11.03
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/55 55
-	1262	438/296	USPAT;	2004/09/14 11:17
			US-PGPUB; EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	324	438/353	USPAT;	2004/09/14 11:21
			US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
_	173	438/361	IBM_TDB USPAT;	2004/09/14 11:23
		1	US-PGPUB;	
			EPO; JPO;	,
			DERWENT;	
			IBM_TDB	
_	203	438/362	USPAT;	2004/09/14 11:26
1			US-PGPUB; EPO; JPO;	
			DERWENT;	·
			IBM TDB	
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_	548	438/221	USPAT;	2004/09/14 11:33
		100,022	US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
_	1539	257/506	USPAT;	2004/09/14 11:48
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	229	257/507	USPAT;	2004/09/14 11:50
			US-PGPUB;	
		•	EPO; JPO;	
			DERWENT;	
		,	IBM TDB	•
-	618	257/508	USPAT;	2004/09/14 11:56
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	298	257/509	USPAT;	2004/09/14 12:00
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1128	257/510	USPAT;	2004/09/14 12:01
			US-PGPUB;	
			EPO; JPO;	
		,	DERWENT;	
			IBM TDB	1